

N-channel 40 V 1.6 mΩ standard level MOSFET in TO220 15 July 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in SOT78 (TO220) using TrenchMOS technology. Product design and manufacture has been optimized for use in battery operated power tools.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Robust construction for demanding applications
- Standard level gate

3. Applications

- Battery-powered tools
- Load switching
- Motor control
- Uninterruptible power supplies

4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	-	150	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	338	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 13		-	1.9	2.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 14	[2]	-	1.3	1.6	mΩ
Dynamic ch	naracteristics						
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 75 A; V _{DS} = 20 V;		-	32	-	nC
Q _{G(tot)}	total gate charge	T _j = 25 °C; <u>Fig. 15</u> ; <u>Fig. 16</u>		-	136	_	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 150 A; V_{sup} ≤ 40 V; unclamped; R_{GS} = 50 Ω; t_p = 0.1 ms; Fig. 3		-	-	1.1	J

[1] Continuous current is limited by package

[2] Measured 3 mm from package.

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UF44
mb	D	drain	TO-220AB (SOT78)	mbb076 S

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMN1R5-40PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN1R5-40PS	PSMN1R5-40PS

PSMN1R5-40PS

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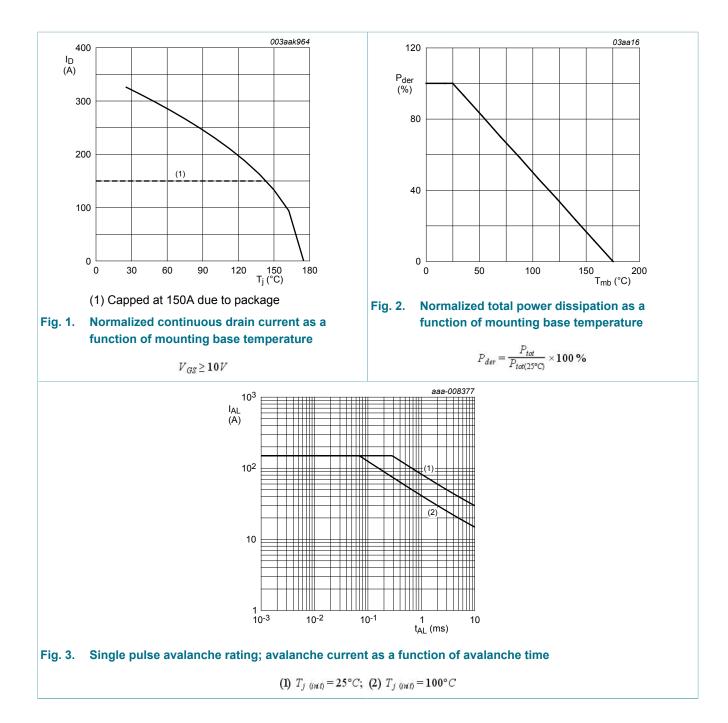
8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

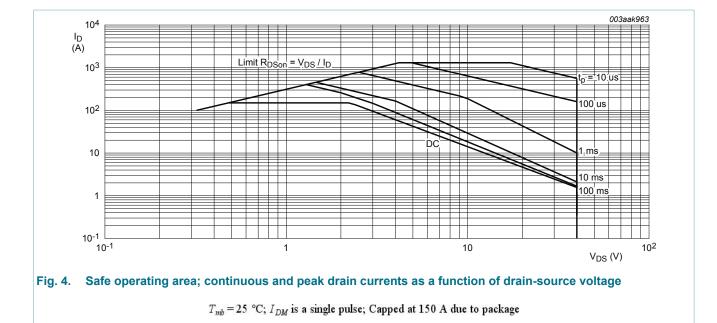
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	40	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	[1]	-	150	А
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	150	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 4		-	1301	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	338	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	150	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	1301	А
Avalanche	ruggedness	-				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; I_{D} = 150 \; A; \\ V_{sup} \leq 40 \; V; \; unclamped; \; R_{GS} = 50 \; \Omega; \\ t_{p} = 0.1 \; ms; \; \underline{Fig. \; 3} \end{array} $		-	1.1	J

[1] Continuous current is limited by package



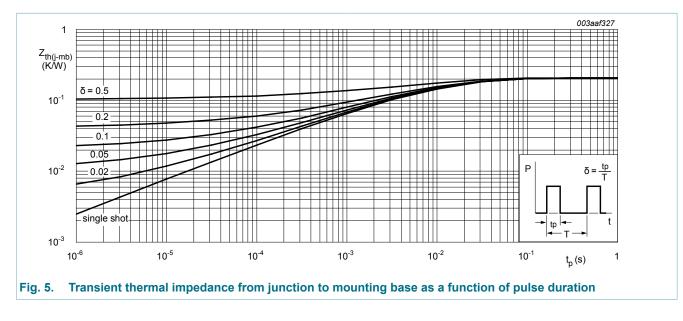
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9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Cymbol	T diameter	Conditions		קני	IIIux	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.22	0.44	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W



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10. Characteristics

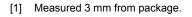
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	cteristics						
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		36	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		40	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; <u>Fig. 11</u>		-	-	4.6	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 11		1	-	-	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = 25 \text{ °C;}$ Fig. 12; Fig. 11		2	3	4	V
I _{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C		-	0.02	10	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C		-	250	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
Doon	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 13		-	1.9	2.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 13		-	2.6	3.2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 14	[1]	-	1.3	1.6	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz		-	1.1	-	Ω
Dynamic ch	aracteristics	1	1				
Q _{G(tot)}	total gate charge	I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V		-	133	-	nC
		I_D = 75 A; V_{DS} = 20 V; V_{GS} = 10 V;		-	136	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 15</u> ; <u>Fig. 16</u>		-	52	-	nC
Q _{GS(th)}	pre-threshold gate- source charge			-	30	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge			-	22.5	-	nC
Q _{GD}	gate-drain charge			-	32	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 75 A; V _{DS} = 20 V; T _j = 25 °C; <u>Fig. 15; Fig. 16</u>		-	6.1	-	V
C _{iss}	input capacitance	V _{DS} = 20 V; V _{GS} = 0 V; f = 1 MHz;		-	9710	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 17</u>		-	2042	-	pF

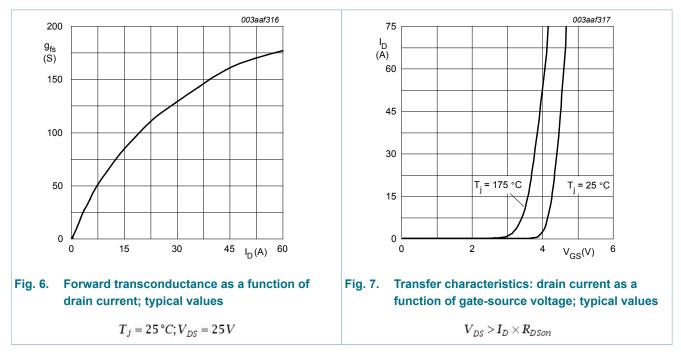
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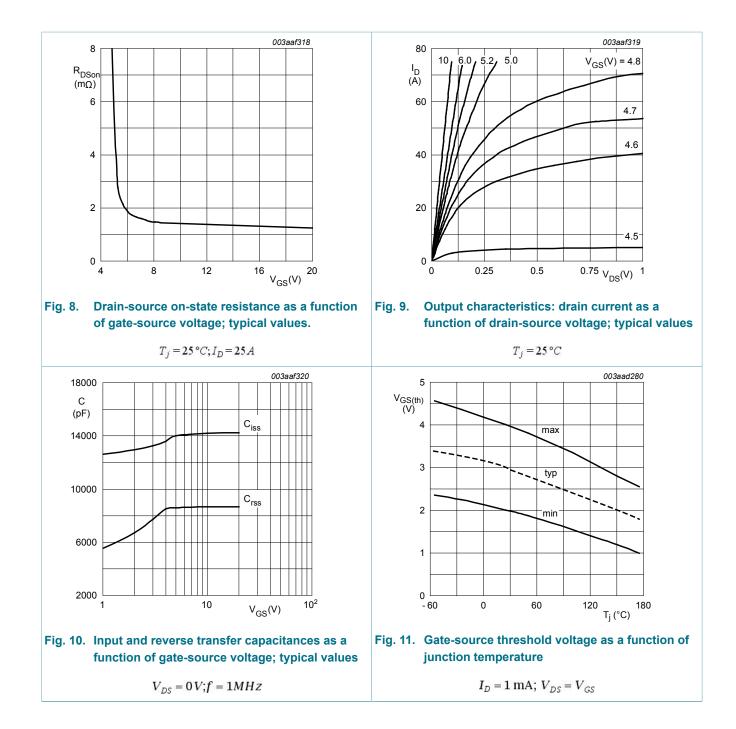
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
C _{rss}	reverse transfer capacitance			-	994	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R _L = 0.8 Ω; V _{GS} = 10 V;		-	45	-	ns
t _r	rise time	R _{G(ext)} = 4.7 Ω; T _j = 25 °C		-	66	-	ns
t _{d(off)}	turn-off delay time			-	111	-	ns
t _f	fall time			-	53	-	ns
Source-drain	n diode				1		
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 18</u>		-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}$		-	64	-	ns
Q _r	recovered charge	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$		-	117	-	nC



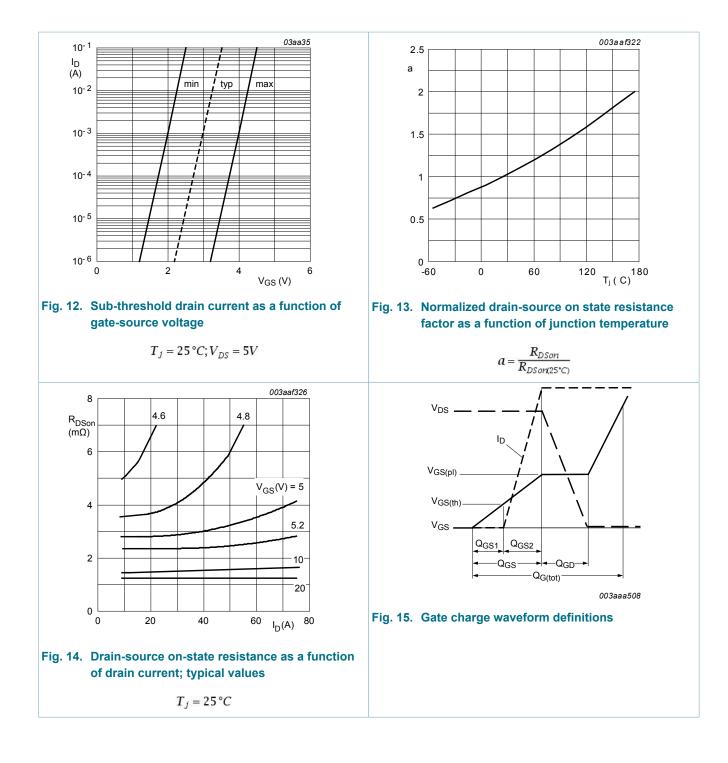


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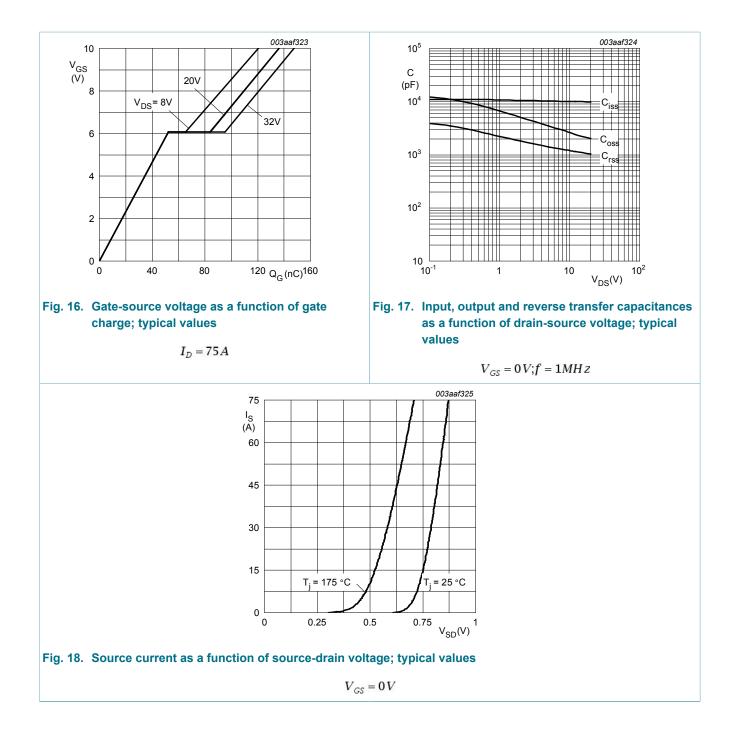


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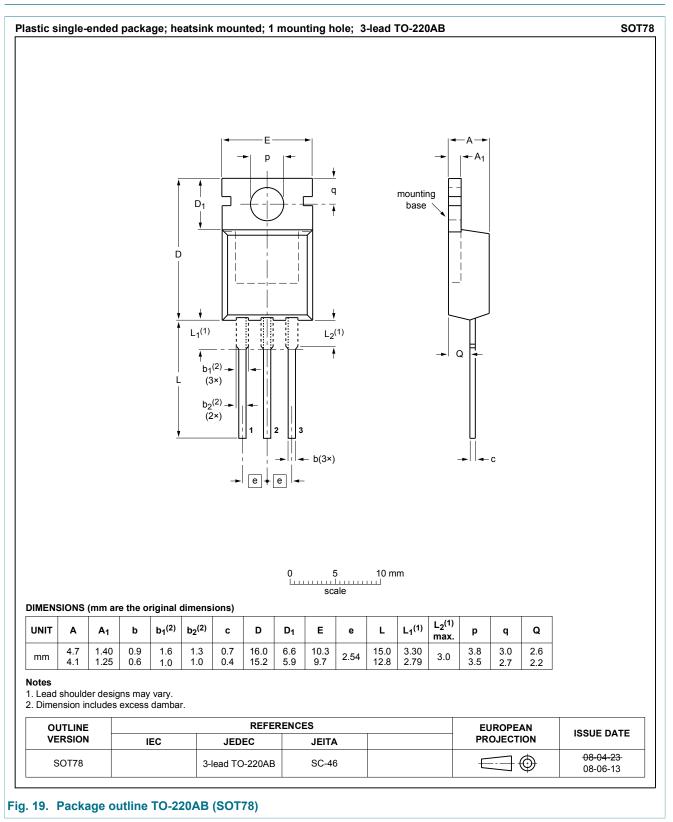


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11. Package outline



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Product data sheet

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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